

Preliminary

BA01232

HBT HYBRID IC

Specifications are subject to change without notice.

DESCRIPTION

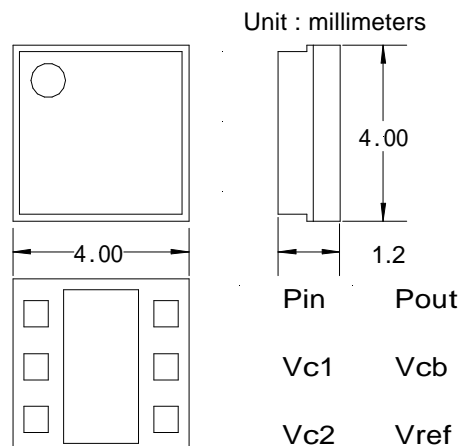
The BA01232 is GaAs RF amplifier designed for W-CDMA hand-held phone.

FEATURES

Low voltage $V_{cc}=3.5V$
 High power $P_o=26.5dBm$ @1920~1980MHz
 High gain $G_p=27.5dB$ @ $P_o=26.5dBm$
 2stage amplifier
 Internal input and output matching
 Small size package 4x4x1.2mm

APPLICATION

W-CDMA(UTRA/FDD) mobile transmitter
 (UE Power Class 3).

OUTLINE DRAWING**ABSOLUTE MAXIMUM RATINGS (Ta=25°C)**

Symbol	Parameter	Condition	Ratings*	Unit
Vcc	Supply voltage of HPA		6	V
Pin	Input power	ZG=ZL=50Ω	7	dBm
Tc(op)	Operating case temp.		-20 ~ +85	°C
Tstg	Storage temp.		-30 ~ +95	°C

*Note : Each maximum rating is guaranteed independently .

ELECTRICAL CHARACTERISTICS(Ta=25°C)

Symbol	Parameter	Test conditions**	Limits			Unit
			MIN	TYP	MAX	
f	Frequency		1920		1980	MHz
Icqt	Idle current	No RF input		35		mA
Ict	Total current			252		mA
PAE	Power added efficiency			50		%
Pin	Input Power	$P_o=26.5dBm$		-1.0		dBm
ρin	Return loss	$V_{c1}=V_{c2}=3.5V$			-6	dB
ACLR	Adjacent channel leakage power at 5MHz	$V_{ref}=2.9V$		-41	-38	dBc
	Adjacent channel leakage power at 10MHz	$V_{cb}=2.9V$		-54	-48	dBc
2Sp/3Sp	2nd/3rd harmonics				-30	dBc
RX noise	RX band noise			-140		dBm/Hz

**NOTE : ZG=ZL=50Ω
 3.84Mcps spreading, HPSK.

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